High–voltage band switching diode

1SS376

●Applications

High voltage switching

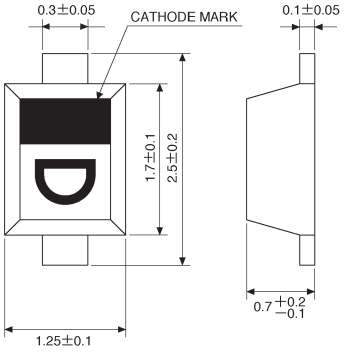
●Features

1) High reliability.
2) Small surface mounting type. (UMD2)
3) Peak reverse voltage guaranteed at 300V with this size.

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



ROHM : UMD2
EIAJ : SC - 76
JEDEC : SOD - 323

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	300	V
DC reverse voltage	V_R	250	V
Peak forward current	I_{FM}	300	mA
Mean rectifying current	I_O	100	mA
Surge current (10ms)	I_{surge}	2	A
Junction temperature	Tj	125	℃
Storage temperature	Tstg	−55∼+125	℃

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditons
Forward voltage	V_F	−	0.97	1.2	V	I_F=100mA
Reverse current	I_R	−	0.03	0.2	μA	V_R=250V
Reverse current	I_R	−	−	100	μA	V_R=300V
Capacitance between terminals	C_T	−	1.2	3	pF	V_R=0V, f=1MHz
Reverse recovery time	trr	−	30	100	ns	I_R=30mA I_F=30mA Irr=3mA

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

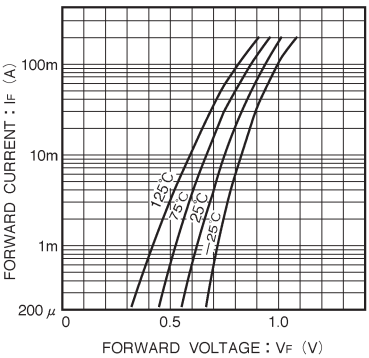


Fig. 1 Forward characteristics

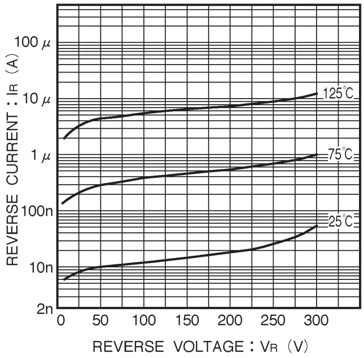


Fig. 2 Reverse characteristics

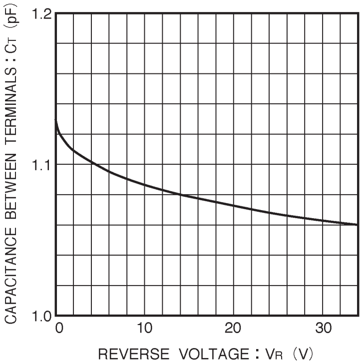


Fig. 3 Capacitance between terminals characteristics

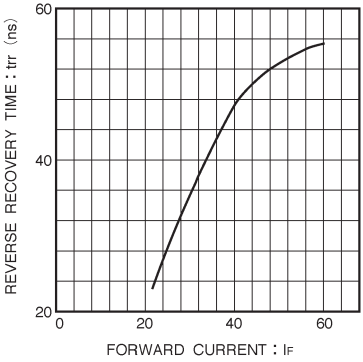


Fig. 4 Reverse recovery time characteristics

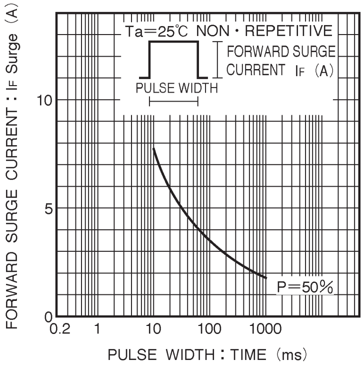


Fig. 5 Surge current characteristics

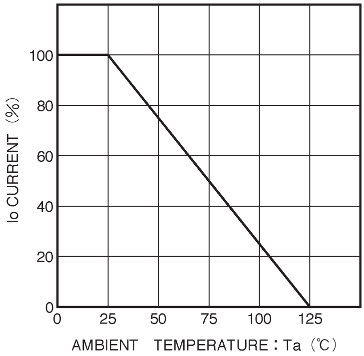


Fig. 6 Derating curve (mounting on glass epoxy PCBs)